

C106 Series

Preferred Devices

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Glassivated PNP devices designed for high volume consumer applications such as temperature, light, and speed control; process and remote control, and warning systems where reliability of operation is important.

- Glassivated Surface for Reliability and Uniformity
- Power Rated at Economical Prices
- Practical Level Triggering and Holding Characteristics
- Flat, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Sensitive Gate Triggering
- Device Marking: Device Type, e.g., C106B, Date Code

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Sine Wave, 50–60 Hz, $R_{GK} = 1\text{ k}\Omega$, $T_C = -40^\circ$ to 110°C)	V_{DRM} , V_{RRM}		Volts
C106B		200	
C106D, C106D1*		400	
C106M, C106M1*		600	
On-State RMS Current (180° Conduction Angles, $T_C = 80^\circ\text{C}$)	$I_T(\text{RMS})$	4.0	Amps
Average On-State Current (180° Conduction Angles, $T_C = 80^\circ\text{C}$)	$I_T(\text{AV})$	2.55	Amps
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, $T_J = +110^\circ\text{C}$)	I_{TSM}	20	Amps
Circuit Fusing Considerations ($t = 8.3\text{ ms}$)	I^2t	1.65	A^2s
Forward Peak Gate Power (Pulse Width $\leq 1.0\text{ }\mu\text{sec}$, $T_C = 80^\circ\text{C}$)	P_{GM}	0.5	Watt
Forward Average Gate Power (Pulse Width $\leq 1.0\text{ }\mu\text{sec}$, $T_C = 80^\circ\text{C}$)	$P_{G(\text{AV})}$	0.1	Watt
Forward Peak Gate Current (Pulse Width $\leq 1.0\text{ }\mu\text{sec}$, $T_C = 80^\circ\text{C}$)	I_{GM}	0.2	Amp
Operating Junction Temperature Range	T_J	-40 to $+110$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to $+150$	$^\circ\text{C}$
Mounting Torque (Note 2)	–	6.0	in. lb.

*D1 signifies European equivalent for D suffix and
M1 signifies European equivalent for M suffix.

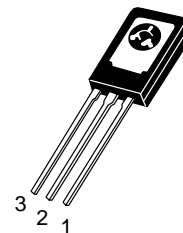
1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
2. Torque rating applies with use of compression washer (B52200F006). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common.



ON Semiconductor®

<http://onsemi.com>

SCRs
4 AMPERES RMS
200 thru 600 VOLTS



TO-225AA
(formerly TO-126)
CASE 077
STYLE 2

PIN ASSIGNMENT	
1	Cathode
2	Anode
3	Gate

ORDERING INFORMATION

Device	Package	Shipping
C106B	TO225AA	500/Box
C106D	TO225AA	500/Box
C106D1*	TO225AA	500/Box
C106M	TO225AA	500/Box
C106M1*	TO225AA	500/Box

*D1 signifies European equivalent for D suffix and
M1 signifies European equivalent for M suffix.

Preferred devices are recommended choices for future use
and best overall value.

C106 Series

THERMAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	75	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current ($V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}, R_{GK} = 1000 \text{ Ohms}$)	I_{DRM}, I_{RRM}	–	–	10	μA
$T_J = 25^\circ\text{C}$ $T_J = 110^\circ\text{C}$		–	–	100	μA

ON CHARACTERISTICS

Peak Forward On-State Voltage (Note 3) ($I_{TM} = 4 \text{ A}$)	V_{TM}	–	–	2.2	Volts
Gate Trigger Current (Continuous dc) (Note 4) ($V_{AK} = 6 \text{ Vdc}, R_L = 100 \text{ Ohms}$)	I_{GT}	–	15	200	μA
$T_J = 25^\circ\text{C}$ $T_J = -40^\circ\text{C}$		–	35	500	
Peak Reverse Gate Voltage ($I_{GR} = 10 \mu\text{A}$)	V_{GRM}	–	–	6.0	Volts
Gate Trigger Voltage (Continuous dc) (Note 4) ($V_{AK} = 6 \text{ Vdc}, R_L = 100 \text{ Ohms}$)	V_{GT}	0.4	0.60	0.8	Volts
$T_J = 25^\circ\text{C}$ $T_J = -40^\circ\text{C}$		0.5	0.75	1.0	
Gate Non-Trigger Voltage (Continuous dc) (Note 4) ($V_{AK} = 12 \text{ V}, R_L = 100 \text{ Ohms}, T_J = 110^\circ\text{C}$)	V_{GD}	0.2	–	–	Volts
Latching Current ($V_{AK} = 12 \text{ V}, I_G = 20 \text{ mA}$)	I_L	–	0.20	5.0	mA
$T_J = 25^\circ\text{C}$ $T_J = -40^\circ\text{C}$		–	0.35	7.0	
Holding Current ($V_D = 12 \text{ Vdc}$) (Initiating Current = 20 mA, Gate Open)	I_H	–	0.19	3.0	mA
$T_J = 25^\circ\text{C}$ $T_J = -40^\circ\text{C}$ $T_J = +110^\circ\text{C}$		–	0.33	6.0	
		–	0.07	2.0	

DYNAMIC CHARACTERISTICS

Critical Rate-of-Rise of Off-State Voltage ($V_{AK} = \text{Rated } V_{DRM}, \text{ Exponential Waveform}, R_{GK} = 1000 \text{ Ohms}, T_J = 110^\circ\text{C}$)	dv/dt	–	8.0	–	$\text{V}/\mu\text{s}$
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3. Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.
4. R_{GK} is not included in measurement.

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Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I_H	Holding Current

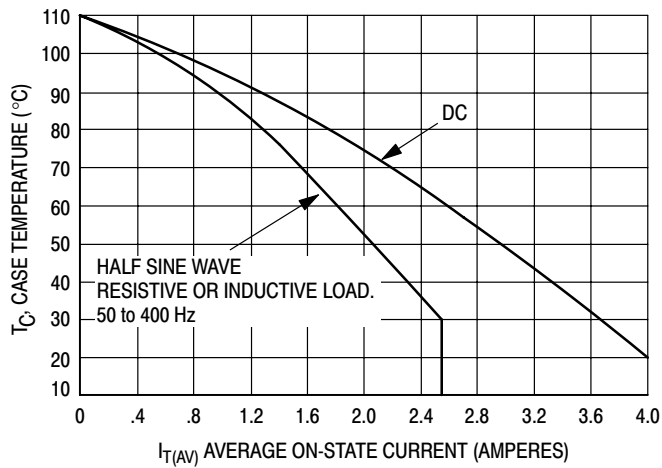
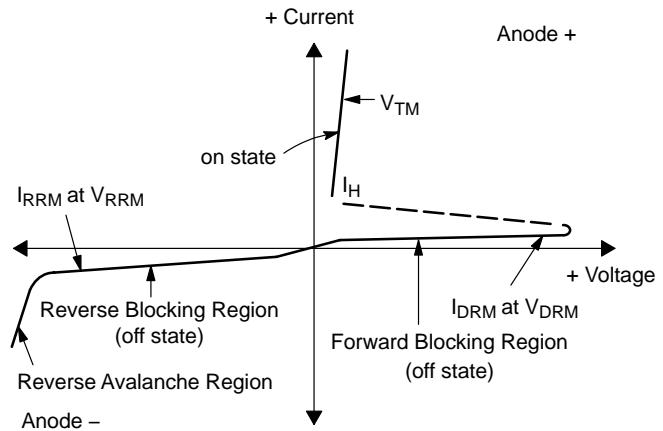


Figure 1. Average Current Derating

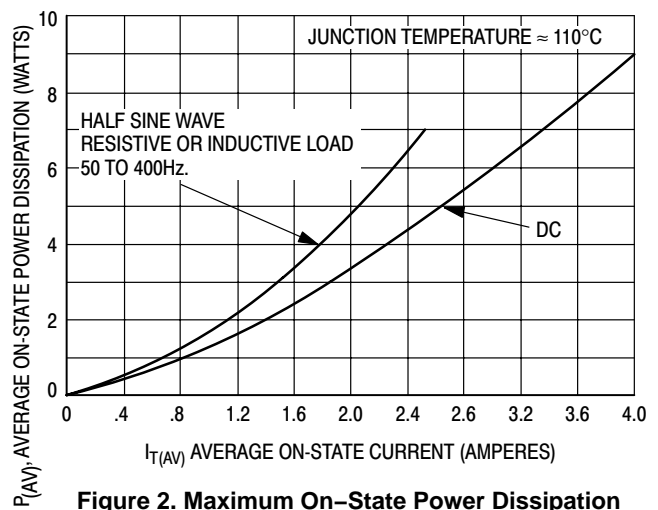


Figure 2. Maximum On-State Power Dissipation

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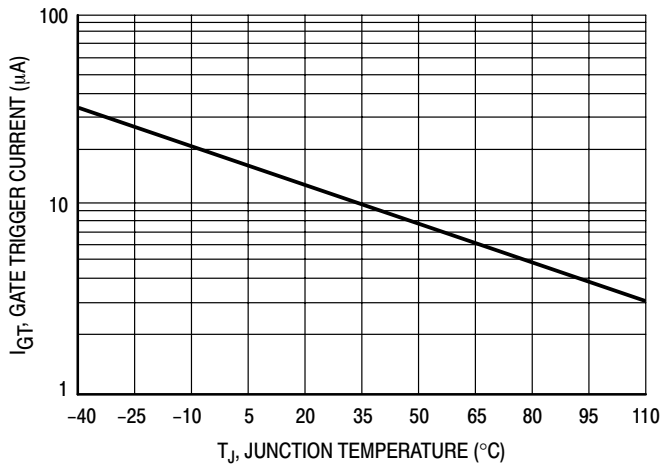


Figure 3. Typical Gate Trigger Current versus Junction Temperature

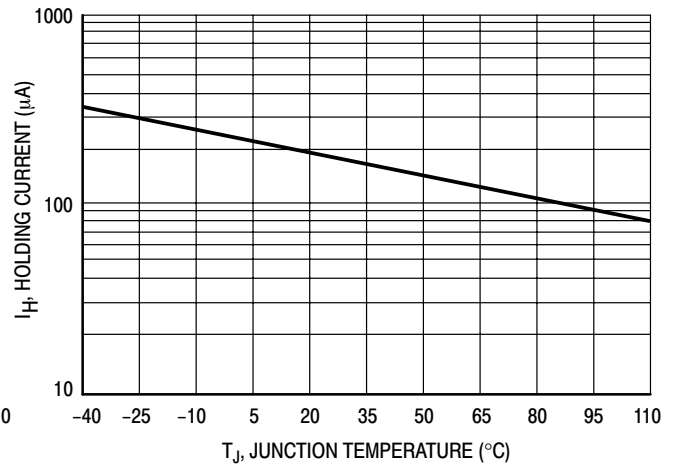


Figure 4. Typical Holding Current versus Junction Temperature

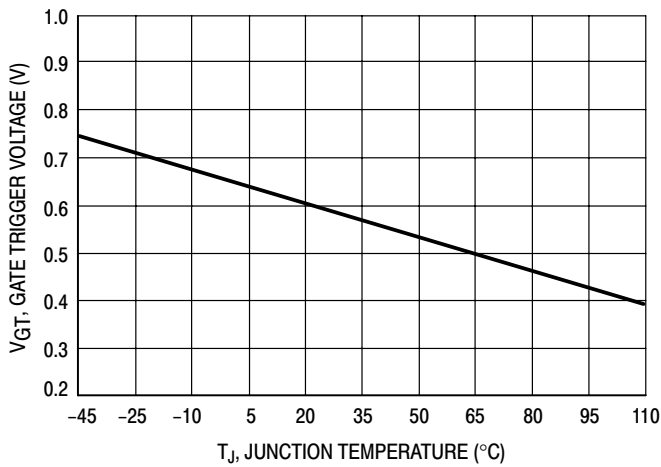


Figure 5. Typical Gate Trigger Voltage versus Junction Temperature

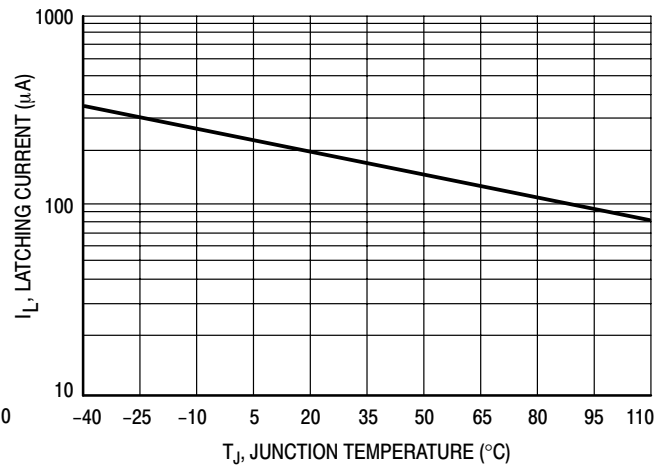
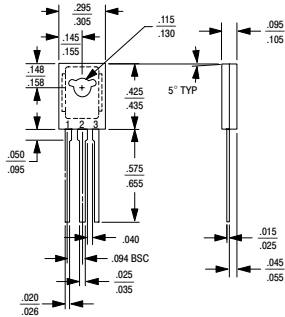


Figure 6. Typical Latching Current versus Junction Temperature

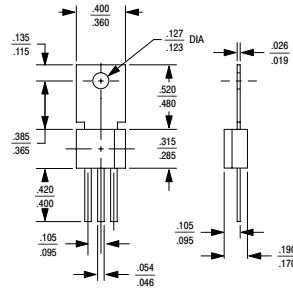
C106 Series

Package Interchangeability

The dimensional diagrams below compare the critical dimensions of the ON Semiconductor C-106 package with competitive devices. It has been demonstrated that the smaller dimensions of the ON Semiconductor package make it compatible in most lead-mount and chassis-mount applications. The user is advised to compare all critical dimensions for mounting compatibility.



ON Semiconductor C-106 Package

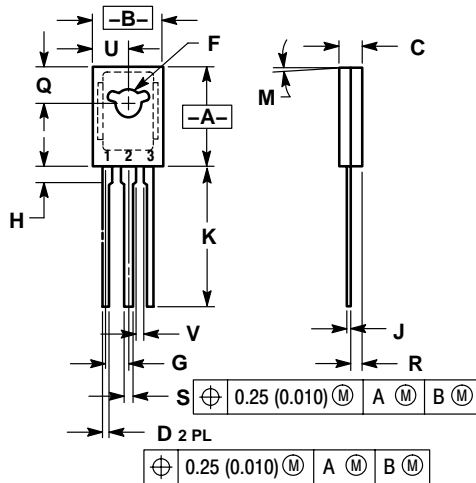


Competitive C-106 Package

C106 Series

PACKAGE DIMENSIONS

TO-225AA (formerly TO-126) CASE 077-09 ISSUE Z




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 2:

1. CATHODE
2. ANODE
3. GATE

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